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February 2015

FPF2488 Dual Channel Over-Voltage Protection Load Switch

Features

Dual Channel Power Switch (V_{BUS} and V_{IF})

■ Surge Protection under IEC 61000-4-5

 $\begin{array}{lll} - & V_{BUS}: \pm 100 \ V \\ - & V_{IF}: \pm 40 \ V \end{array}$

Input Voltage Range

V_{BUS}: 2.5 V ~ 23 VV_{IF}: 3.1 V ~ 5.5 V

Max Continuous Current Capability

V_{BUS}: 2.5 AV_{IF}: 6 A

Ultra Low On-Resistance

- V_{BUS} : Typ. 33 mΩ - V_{IF} : Typ. 10 mΩ

Over Voltage Protection

V_{BUS}: 10 V ± 100 mV
 V_{IF}: 5.25 V ± 250 mV

LDO Output based V_{BUS_DET} for V_{BUS} Detection

Active Low Control for V_{BUS} Path

OTG Functionality on V_{BUS} Path

Conditional Active High Control for V_{IF} Path

■ Reverse-Current Blocking for V_{IF} Path

Applications

- Mobile Handsets and Tablets
- Wearable Devices

Description

The FPF2488 features a 2-channel power switch, which offers surge protection and Over-Voltage Protection (OVP), to protect downstream components and enhancing overall system robustness.

Channel one (V_{BUS}) is an active-low, 28 V/2.5 A rated, power MOSFET switch with an internal clamp supporting ± 100 V surge protection, highly accurate fixed OVP at 10.0 V (± 100 mV), and OTG functionality. Channel two (V_{IF}) is a conditional active-high, 6 V/6 A rated, power MOSFET switch with an integrated TVS supporting \pm 40 V surge protection and fixed OVP at 5.25 V (\pm 250 mV). V_{IF} also provides Reverse Current Blocking (RCB) during its OFF state to minimize leakage current.

V_{BUS_DET} is paired with always ON LDO to power downstream devices even with VBUS is greater than 2.5 V, even when disabled through the ONB pin. This provides power sequence control or a host controlled configuration in system.

The FPF2488 is available in a 15-bump, 1.6 mm x 2.2 mm Wafer-Level Chip-Scale Package (WLCSP) with 0.4 mm pitch.

Related Resources

http://www.fairchildsemi.com/

Ordering Information

Part Number	Operating Temperature Range	Top Mark	Top Mark Package	
FPF2488UCX	-40°C – +85°C	GW	15-Ball, 0.4 mm Pitch WLCSP	Tape & Reel

Application Diagram

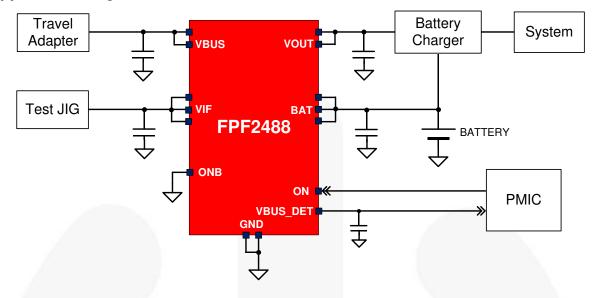


Figure 1. Typical Application

Block Diagram

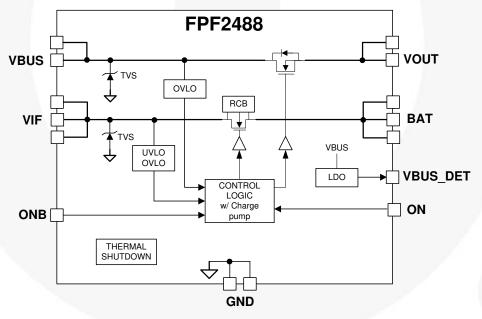
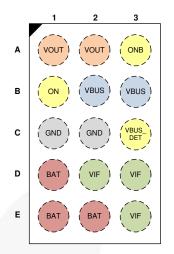


Figure 2. Functional Block Diagram

Pin Configuration



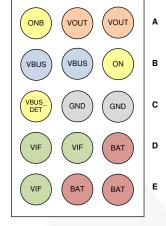


Figure 3. Pin Configuration (Top View)

Figure 4. Pin Configuration (Bottom View)

Pin Definitions

Name	Bump	Туре	Description	
V _{BUS}	B2, B3	Input/Supply	Switch Input and Device Supply	
VOUT	A1, A2	Output	Switch Output to Load	
V _{IF}	D2, D3, E3	Input/Supply	Switch Input and Device Supply	
BAT	D1, E1, E2	Output	Switch Output to Battery	
V _{BUS_DET}	C3	Output	Regulated Output according to V _{BUS}	
ON	B1	Input	Active HIGH: V _{IF} path only and when BAT is valid prior to V _{IF}	
ONB	A3	Input	Active LOW: V _{BUS} path only	
GND	C1, C2	GND	Ground	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Min.	Max.	Unit		
V _{BUS}	V _{BUS} to GND & V _{BUS} to VOU		-0.3	29.0	٧	
V _{IF}	V _{IF} to GND	2		-2 ⁽¹⁾	6	٧
V _{OUT}	V _{OUT} to GND			-0.3	$V_{IN} + 0.3$	٧
BAT	BAT to GND			-0.3	V _{IF} + 0.3	V
V _{BUS_DET}	V _{BUS_DET} to GND				8	V
V _{ON(B)}	ONB or ON to GND				6	V
1	Continuous V _{BUS} Current				2.5	Α
I _{IN_VBUS}	Peak V _{BUS} Current (5 ms)		- //		5	Α
	Continuous V _{IF} Current				6	Α
I _{IN_VIF}	Peak V _{IF} Current (5 ms)				12	Α
I _{IN_VBUS_DET}	Continuous V _{BUS_DET} Current		1	mA		
t _{PD}	Total Power Dissipation at T		1.54	W		
T _{STG}	Storage Temperature Range	-65	+150	°C		
T_J	Maximum Junction Tempera		+150	°C		
TL	Lead Temperature (Soldering		+260	°C		
Θ_{JA}	Thermal Resistance, Junctio		81 ⁽²⁾	°C/W		
		IEC 61000-4-2 System	Air Discharge	15.0		
		Level ESD	Contact Discharge	8.0		
ESD	Electrostatic Discharge	Human Body Model, ANSI/ESDA/JEDEC JS- 001-2012	All Pins	2		kV
	Capability	Charged Device Model, JESD22-C101 All Pins		1		
Surge		IEC 61000-4-5,	V _{BUS}	±100		V
Surge		Surge Protection	V _{IF}	±40		

Notes:

- 1. Pulsed, 50 ms maximum non-repetitive.
- 2. Measured using 2S2P JEDEC std. PCB.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter		Max.	Unit
V _{BUS}	Supply Voltage, V _{BUS}		23.0	V
V _{IF}	Supply Voltage, V _{IF}		5.5	V
C _{IN} / C _{OUT}	Input and Output Capacitance			μF
C _{VBUS_DET}	Output Capacitance			μF
T _A	Operating Temperature	-40	+85	°C

Electrical Characteristics

Unless otherwise noted, V_{BUS} =2.5 to 23 V, V_{IF} =3.1 to 5.5 V, T_{A} =-40 to 85°C; Typical values are at V_{BUS} =5 V, $I_{IN} \le 2$ A, V_{IF} =4 V, C_{IN} =0.1 μF and T_{A} =25°C.

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Basic Operat	tion	,	I	I	ı	
	Input Quiescent Current	V _{BUS} =5 V, ONB=0 V, V _{BUS_DET} =Floating		160	250	μА
lQ		V _{IF} =4 V		100	150	μΑ
1	0)#00	V _{BUS} =12 V, V _{OUT} =0 V, V _{BUS} _DET=Floating		150	205	μA
I _{IN_Q}	OVLO Supply Current	V _{IF} =5.5 V, BAT=0 V		100	180	μΑ
T_{SDN}	Thermal Shutdown ⁽³⁾			140		°C
T _{SDN_HYS}	Thermal Shutdown Hysteresis ⁽³⁾			20		°C
V _{BUS} to VOL	JT Switch				•	
V _{BUS_CLAMP}	Input Clamping Voltage	I _{IN} =10 mA		35		V
	Over Welter or Trial Level	V _{BUS} Rising, T _A =-40 to 85°C	9.9	10.0	10.1	V
V_{BUS_OVLO}	Over-Voltage Trip Level	V _{виs} Falling, T _{A=} -40 to 85°C	9.8			V
_ /	0.0.11	V _{BUS} =5 V, I _{OUT} =1 A, T _A =25°C		33	39	mΩ
R _{ON_VBUS}	On-Resistance	V _{BUS} =9 V, I _{OUT} =1 A, T _A =25°C		33	39	mΩ
t _{DEB_VBUS}	Debounce Time	Time from V _{BUS_MIN} < V _{BUS} < V _{BUS_OVLO} to V _{OUT} =0.1 × V _{BUS}		15		ms
tstart vbus	Soft-Start Time	Time from V _{BUS} =V _{BUS} MIN to 0.1 × V _{BUS} DET		30	À	ms
t _{ON_VBUS}	Switch Turn-On Time	$R_L {=} 100~\Omega,~C_L {=} 22~\mu F,~V_{OUT}~from~0.1~\times~V_{BUS}$ to $0.9~\times~V_{BUS}$	Y	3		ms
t _{OFF_VBUS}	Switch Turn-Off Time	$R_L=100~\Omega,~No~C_L,~V_{BUS}>V_{BUS_OVLO}~to$ $V_{OUT}=0.8\times V_{BUS}$			150	ns
V _{IF} to BAT S	Switch				•	
V _{IF_CLAMP}	Input Clamping Voltage	I _{IN} =10 mA		6.4		V
M	Hadaa Waltana Tria Laval	V _{IF} Rising, T _A =-40 to 85°C		2.85	3.05	V
V_{IF_UVLO}	Under-Voltage Trip Level	V _{IF} Falling, T _A =-40 to 85°C		2.7		V
V	Over Veltage Trip Level	V _{IF} Rising, T _A =-40 to 85°C	5.00	5.25	5.50	٧
V_{IF_OVLO}	Over-Voltage Trip Level	V _{IF} Falling, T _A =-40 to 85°C	4.8			V
R _{ON_VIF}	On-Resistance	V _{IF} =3.1 V, I _{OUT} =1 A, T _A =25°C		10	15	mΩ
I _{RCB}	Reverse Current	V _{IF} =0 V, BAT=4.4 V		3	7	μΑ
t _{DEB_VIF}	Debounce Time	Time from $V_{IF_UVLO} < V_{IF} < V_{IF_OVLO}$ to BAT=0.1 \times V_{IF}		15		ms
tqual_vif	Qualification Time	BAT > V _{IH_BAT} First, Time from ON > V _{IH_ON(B)} to BAT Voltage Increase		30		ms
t _{ON_} vif	Switch Turn-On Time	$R_L{=}100~\Omega,~C_L{=}22~\mu\text{F},~V_{OUT}~\text{from}~0.1~\times~\text{VIF}~\text{to}\\0.9~\times~\text{VIF}$		3	1	ms
toff_vif	Switch Turn-Off Time	$R_L{=}100~\Omega,~No~C_L,V_{IN}>V_{OVLO}$ to $V_{OUT}{=}0.8~\times~VIF$			150	ns

Note:

3. Guaranteed by characterization and design.

Continued on the following page...

Electrical Characteristics

Unless otherwise noted, V_{BUS} =2.5 to 23 V, V_{IF} =3.1 to 5.5 V, T_{A} =-40 to 85°C; Typical values are at V_{BUS} =5 V, $I_{IN} \le 2$ A, V_{IF} =4 V, C_{IN} =0.1 μF and T_{A} =25°C.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
V _{BUS_DET}							
			V _{BUS} =6.5 V, I _{BUS_DET} =0 mA, T _A =25°C	6.0		6.5	٧
V	V Outrot Valtage		V _{BUS} =15 V, I _{BUS_DET} =0 mA, T _A =25°C	6.0	7.0	7.9	V
V_{BUS_DET}	V _{BUS_DET} Output Voltage		V _{BUS} =6.5 V, I _{BUS_DET} =1 mA, T _A =25°C	6.0	6.3	6.5	٧
			V _{BUS} =15 V, I _{BUS_DET} =1 mA, T _A =25°C	6.0	7.0	7.9	٧
Digital Signal	s						
V _{IH_ON(B)}	Enable HIGH Voltage		V _{BUS} , V _{IF} Operating Range	1.2			V
$V_{\text{IL_ON(B)}}$	Enable LOW Voltage		V _{BUS} , V _{IF} Operating Range			0.5	٧
V _{IH_BAT}	BAT Presence HIGH Voltag	ge	BAT Rising	2.6			V
V_{IL_BAT}	BAT Presence Low Voltage)	BAT Falling			1.7	٧
I _{VBUS_DET_LEAK}	V _{BUS_DET} Leakage Current		V _{VBUS_DET} =5 V, V _{BUS} =0 V			1	μΑ
O _{NB_Leak}	ONB Leakage Current		V _{BUS} =5 V, V _{OUT} =Float			1	μΑ

Timing Diagrams

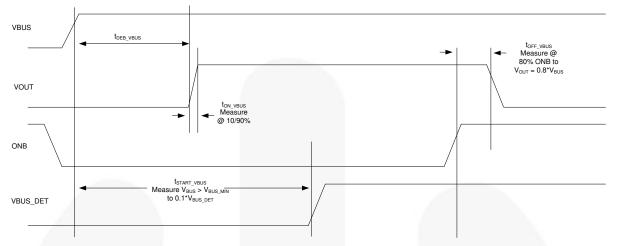


Figure 5. Timing for V_{BUS} Power Up/Down and Normal Operation

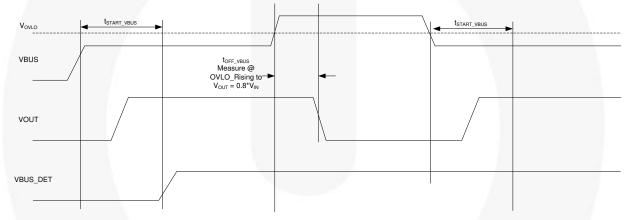


Figure 6. Timing for V_{BUS} OVLO Operation (ONB=LOW)

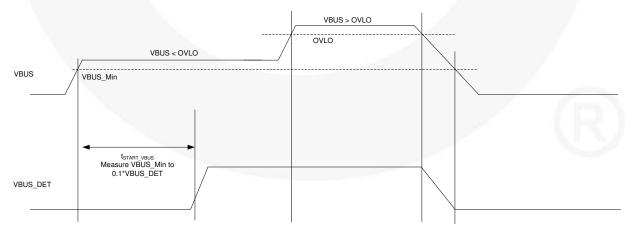


Figure 7. Always ON V_{BUS_DET} Operation (ONB=HIGH)

Timing Diagrams (Continued)

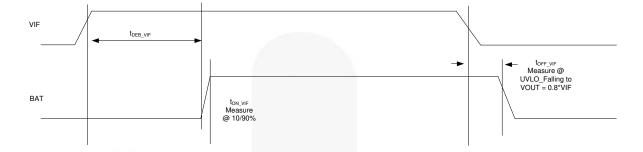


Figure 8. Timing for V_{IF} Power Up/Down and Normal Operation (ON=Don't Care)

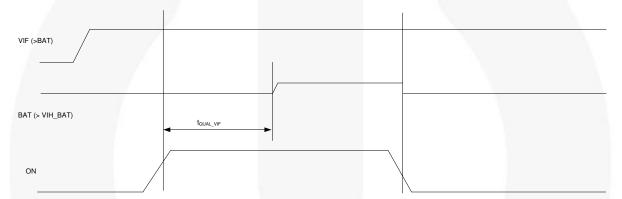


Figure 9. Timing for V_{IF} Power Up/Down and Normal Operation with ON Pin

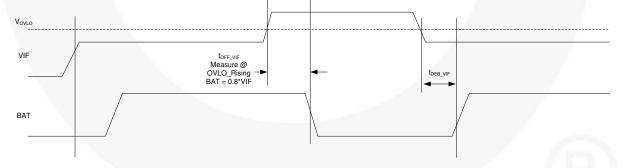


Figure 10. Timing for VIF OVLO Operation (ON=Don't Care)

V_{IF} Turn-On Qualification State Diagram

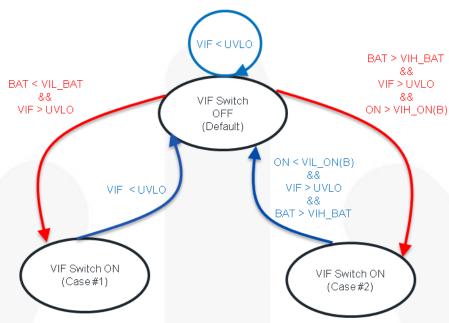


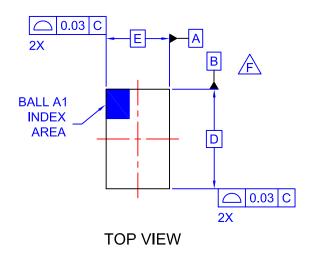
Figure 11. V_{IF} Turn-On Qualification State Diagram

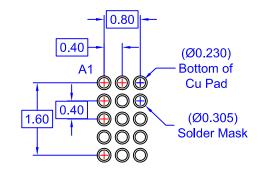
Notes:

- 4. Case #1 is reflecting removable battery system without ON signal.
- 5. Case #2 is reflecting embedded battery system with ON signal.

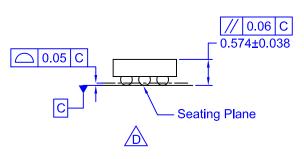
Product-Specific Dimensions

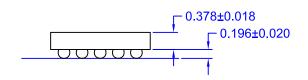
D	E	X	Y
2200 μm ±30 μm	1600 μm ±30 μm	400 μm ±18 μm	300 μm ±18 μm



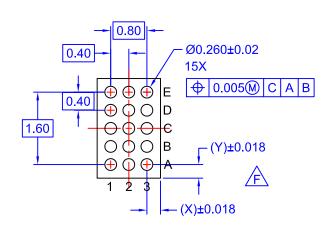


RECOMMENDED LAND PATTERN (NSMD TYPE)





SIDE VIEWS



BOTTOM VIEW

NOTES

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASMEY14.5M, 2009.
- D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- E. PACKAGE NOMINAL HEIGHT IS 574 ± 38 MICRONS (536-612 MICRONS).
- F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.
- G. DRAWING FILNAME: MKT-UC015AC REV2.



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